

EAST - (S 2450) - Amorphous and Monocrystalline Gels FET wip 1)			Search Text		Time Stamp	
Line	File	Text	DR	Time Stamp		
1	3489	257/52,410,411.ccls.) (438/482,216,261,421,591,595,287,954,981.ccls.	USPAT; US-PGPUB;	2001/12/20		
2	175	((fet or (field adj effect adj transistor)) and ((gate same amorphous) and (gate same (monocrystalline or	EPO; JPO; DERWENT;	13:54		
3	11	monocrystal))) and (257/52,410,411.ccls.) (438/482,216,261,421,591,595,287,954,981.ccls.)	USPAT; US-PGPUB;	2001/12/18		
4	97	((fet or (field adj effect adj transistor)) and ((gate same amorphous) and (gate same (monocrystalline or	EPO; JPO; DERWENT;	10:30		
5	8	monocrystal))) and (257/52,410,411.ccls.) (438/482,216,261,421,591,595,287,954,981.ccls.)	USPAT; US-PGPUB;	2001/12/18		
6	3	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	EPO; JPO; DERWENT;	10:25		
7	68	and (257/52,410,411.ccls.) (438/482,216,261,421,591,595,287,954,981.ccls.)	USPAT; US-PGPUB;	2001/12/18		
8	7	4479297.pn.	EPO; JPO; DERWENT;	10:45		
9	9	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	USPAT; US-PGPUB;	2001/12/18		
10	5	and (barium or strontium or titanium or lanthanum or zirconium or aluminum)	EPO; JPO; DERWENT;	10:48		
11	2	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	USPAT; US-PGPUB;	2001/12/28		
12	45	and (barium or strontium or titanium or lanthanum or zirconium or aluminum)	EPO; JPO; DERWENT;	09:33		
13	2	("5393352" "5514484" "5830270" "5482003" "5450812" "5225031" "6022140" "6023082" "5767543").pn.	USPAT; US-PGPUB;	2001/12/18		
14	6	("5393352" "5514484" "5830270" "5482003" "5450812" "5225031" "6022140" "6023082" "5767543").pn.	EPO; JPO; DERWENT;	10:47		
15	2	("5393352" "5514484" "5830270" "5482003" "5450812" "5225031" "6022140" "6023082" "5767543").pn.	USPAT; US-PGPUB;	2001/12/28		
16	2	("JP 08012494 A"	EPO; JPO; DERWENT;	09:37		
17	1	("4523211" "5478653" "3802967" "4404265" "4482906" "4846926" "4882300" "4891091" "4928154" "4963949"	USPAT	2001/12/19		
18	1	"4999842" "5141894" "5155658" "5159413" "5221367" "5248564" "5270298" "5310707" "5326721" "5418389" "5556463"	USPAT; US-PGPUB;	11:02		
19	1	"de 4120258 A1"	EPO; JPO; DERWENT;	2001/12/19		
20	12	"EP 250171 A1" "ep 342937 A1" "ep 455526 A1" "ep 602568 A1" "EP 607435 A1" "EP 1001468 A1" "EP 514018 A1" "ep	USPAT; US-PGPUB;	11:10		
21	24	999600 A1"	EPO; JPO; DERWENT;	2001/12/20		
22	3	5347157.pn.	USPAT	14:16		
23	1988	5221413.pn.	USPAT; US-PGPUB;	2001/12/20		
24	0	"ep 999600"	EPO; JPO; DERWENT;	14:15		
25	7	"gb 1319311"	USPAT; US-PGPUB;	2001/12/20		
26	1	"jp 06291299"	EPO; JPO; DERWENT;	14:22		
27	1	"jp 06291299" "jp 01123866" "jp 01126083" "jp 02000039" "jp 05048072" "jp 05208835" "jp 05413455" "jp	USPAT; US-PGPUB;	2001/12/20		
28	1	05508742" "jp 06110818" "jp 06232126" "jp 06303499" "jp 06313110" "jp 06319836" "jp 06334168" "pct 09914804"	EPO; JPO; DERWENT;	14:29		
29	1	"jp 06291299" "jp 01123866" "jp 01126083" "jp 02000039" "jp 05048072" "jp 05208835" "jp 05413455" "jp	USPAT; US-PGPUB;	2001/12/20		
30	1	05508742" "jp 06110818" "jp 06232126" "jp 06303499" "jp 06313110" "jp 06319836" "jp 06334168" "pct 09914804"	EPO; JPO; DERWENT;	14:32		
31	1	"wo 9914804" "wo 9963580"	USPAT; US-PGPUB;	14:35		
32	1	relative adj permittivity	EPO; JPO; DERWENT;	2001/12/20		
33	0	4479297.pn. and (relative adj permittivity)	USPAT; US-PGPUB;	14:36		
34	7	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	EPO; JPO; DERWENT;	2001/12/20		
35	1	and (barium or strontium or titanium or lanthanum or zirconium or aluminum) and ((257/52,410,411.ccls.) (438/	USPAT; US-PGPUB;	14:37		
36	1	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	EPO; JPO; DERWENT;	14:40		
37	1	and (barium or strontium or titanium or lanthanum or zirconium or aluminum) and ((257/52,410,411.ccls.) (438/	USPAT; US-PGPUB;	2001/12/20		
38	1	4479297.pn. and (relative adj permittivity)	EPO; JPO; DERWENT;	14:59		
39	1	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	USPAT; US-PGPUB;	15:01		
40	1	and (barium or strontium or titanium or lanthanum or zirconium or aluminum) and ((257/52,410,411.ccls.) (438/	EPO; JPO; DERWENT;	2001/12/20		
41	1	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	USPAT; US-PGPUB;	15:04		
42	1	and (barium or strontium or titanium or lanthanum or zirconium or aluminum) and ((257/52,410,411.ccls.) (438/	EPO; JPO; DERWENT;	2001/12/28		
43	1	4479297.pn. and (relative adj permittivity)	USPAT; US-PGPUB;	09:33		
44	1	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	USPAT; US-PGPUB;	2001/12/28		
45	1	and (barium or strontium or titanium or lanthanum or zirconium or aluminum) and ((257/52,410,411.ccls.) (438/	EPO; JPO; DERWENT;	09:34		
46	1	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	USPAT; US-PGPUB;	2001/12/28		
47	1	and (barium or strontium or titanium or lanthanum or zirconium or aluminum) and ((257/52,410,411.ccls.) (438/	EPO; JPO; DERWENT;	09:38		
48	1	4479297.pn. and (relative adj permittivity)	USPAT; US-PGPUB;	2001/12/28		
49	1	((fet or (field adj effect adj transistor)) and ((gate same amorphous same (monocrystalline or monocrystal))	EPO; JPO; DERWENT;	09:38		
50	1	and (barium or strontium or titanium or lanthanum or zirconium or aluminum) and ((257/52,410,411.ccls.) (438/	USPAT; US-PGPUB;	2001/12/28		
51	1	4479297.pn. and (relative adj permittivity)	EPO; JPO; DERWENT;	09:38		

EAST Search 12/28/01